L Number	Hits	Search Text	DB	Time stamp
-	1515	gate near100 (reces$4 groov$3) near100 substrate	USPAT; US-PGPUB	2003/12/03 18:14
-	119	(gate near100 (reces$4 groov$3) near100 substrate) and ((silicon near3 germanium) Si?Ge Si-Ge SiGe)	USPAT; US-PGPUB	2003/12/03 18:14
-	24755	((silicon near3 germanium) Si?Ge Si-Ge SiGe)	USPAT; US-PGPUB	2003/12/03 18:14
-	8216	gate near100 (reces$4 groov$3 open$4 trench) near100 substrate	USPAT; US-PGPUB	2003/12/03 18:14
-	19782	gate same (reces$4 groov$3 open$4 trench) same substrate	USPAT; US-PGPUB	2003/12/03 18:15
-	8237	gate with (reces$4 groov$3 open$4 trench) with substrate	USPAT; US-PGPUB	2003/12/03 18:15
-	19782	(gate near100 (reces$4 groov$3 open$4 trench) near100 substrate) (gate same (reces$4 groov$3 open$4 trench) same substrate) (gate with (reces$4 groov$3 open$4 trench) with substrate)	USPAT; US-PGPUB	2003/12/03 18:15
-	1619	(((silicon near3 germanium) Si?Ge Si-Ge SiGe)) and ((gate near100 (reces$4 groov$3 open$4 trench) near100 substrate) (gate same (reces$4 groov$3 open$4 trench) same substrate) (gate with (reces$4 groov$3 open$4 trench) with substrate))	USPAT; US-PGPUB	2003/12/03 18:16
-	4	(("6214679") or ("5624869") or ("5883003") or ("6037922")).PN.	USPAT; US-PGPUB	2003/12/04 10:03
-	45	"6214679" "5624869" "5883003" "6037922"	USPAT; US-PGPUB	2003/12/04 10:03
-	1623	(((silicon near3 germanium) Si?Ge Si-Ge SiGe)) and ((gate near100 (reces$4 groov$3 open$4 trench) near100 substrate) (gate same (reces$4 groov$3 open$4 trench) same substrate) (gate with (reces$4 groov$3 open$4 trench) with substrate))	USPAT; US-PGPUB	2003/12/04 10:22
-	38	(((silicon near3 germanium) Si?Ge Si-Ge SiGe)) and ((gate near100 (reces$4 groov$3 open$4 trench) near100 substrate) (gate same (reces$4 groov$3 open$4 trench) same substrate) (gate with (reces$4 groov$3 open$4 trench) with substrate))	EPO; JPO; DERWENT; IBM_TDB	2003/12/04 10:23
-	653	anisotropic$6 near100 etch$3 near100 (substrate wafer) near100 gate	EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:20
-	0	(anisotropic$6 near100 etch$3 near100 (substrate wafer) near100 gate) and ((silicon near3 germanium) Si-Ge Si?Ge SiGe)	EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:19